

ABSTRACT

Gate dielectric structures for integrated circuits and methods for manufacturing such gate dielectric structures are described. The gate dielectric structures contain gate oxide layers that are provided using a low temperature in-situ steam generation process, thereby providing silicon oxide layers of a very high quality. The gate oxide layers are used primarily in thin film transistors and as the bottom layer in the gate dielectric of silicon-oxide-nitride-oxide-silicon semiconductor devices.

2006 FEB 20 2 44 PM '02